Monolithic Digital IC



LB1890M

FDD Spindle Motor Driver

Overview

The LB1890M is a 3-phase DD motor driver IC and is an ideal FDD spindle motor driver for 3.5 inch applications.

Functions and Features

- Three phase total wave linear driver
- Eliminates need for output electrolytic capacitor (however, depending on the motor, this may not apply)
- On-chip digital speed control
- Start/stop circuit
- Current limiter circuit
- On-chip index comparator (single HYS)
- On-chip index delay circuit
- AGC circuit
- Temperature protection circuit

Package Dimensions

unit: mm **3129-MFP36S**





Specifications

Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Maximum supply voltage	V _{CC} max		7.0	V
Maximum output current	I _O max1	t≦0.5	1.0	А
Steady Maximum output current	I _O max2		0.7	А
Allowable power dissipation	Pd max	Independent IC	1	W
Operating temperature	Topr		-20 to +80	°C
Storage temperature range	Tstg		-40 to +150	°C

Allowable Operating Conditions at $Ta=25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage range	V _{CC}		4.2 to 6.5	V

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Electrical Characteristics at Ta = 25°C, V_{CC} = 5V

_			Ratings				
Parameter	Symbol	Conditions	min	typ	max	Unit	Note
	lcco1	$V_{CC} = 5.0V$ (Stop)		,,	0.2	mA	
Current drain		$V_{CC} = 5.0V$ (Steady)		20	30	mA	
Time changeover bias current	 				0.4	mA	
Time changeover input voltage 1	Veu		0		0.8	v	
Time changeover input voltage 2	Veill		2.0		Vcc	v	
S/S1 bias current	le/e1				0.4	mA	
S/S1 start voltage	Ve/e1		2.0		Vcc	v	
S/S1 stop voltage	Ve/e1		0		0.8	v	
S/S2 bias current	le/e2				0.1	mA	
S/S2 start voltage	Ve/62		0		0.8	v	
S/S2 stop voltage	Ve/e2		2.0		Vcc	V	
Hall-effect bias amplifier input current	- 5/52 Jup		2.0		20	υA	
In-phase input voltage range	Vh		22		$V_{00} = 0.7$	V	
Differential input voltage range	Vdif		70		250	m\/n-n	*2
	Vho				+1.0	mV	*1
Hall-Effect output voltage	Vii	l – 5mA		15	1.0	V	
	<u>чн</u> Б.,	Stop		1.0	+10	114	
	'HL Vsat1	$l_{0} = 0.354$ $V_{00} = 4.2V$		12	1.4	μ/(
(Sink plus source)	Vsat2	$l_0 = 0.704$ V $l_0 = 4.2V$		1.2	2.0	V	
Outout leak current		10 = 0.101, 400 = 4.24		1.0	+1.0	mA	
Current limiter	Vrof1		0.27	0.30	0.33	11#X	
Control amplifier voltage gain	G		0.21	0.00	0.00	dB	
				-0	.1	dD	
Integrated emplifier integral reference voltage				V /0	±I	ив	
Integrated amplifier internal reference voltage	Vieiz			VCC/2		V	
Integrated amplifier blas current				0.75	±1	μΑ	
Integrated output voltage amplitude	Vi-	II = -0.5 mA with reference of Vref2		-1.4		V	
Gain band width				1000		kHz	*1
FG amplifier input voltage	V _{EG}		5		100	mVp-p	
FG amplifier voltage gain	G _{FG}	Open loop		60		dB	*1
FG amplifier input offset	V _{FG} 0				±10	mV	
FG amplifier internal reference voltage	VEGR		2.20	2.50	2.80	V	
	∆Vsh1	"H" → "L"		25		mV	*1
Schmitt hysteresis width	∆Vsh2	$``L" \to ``H"$		25		mV	*1
Schmitt input operation level	Vsh		1		V _{CC} -1	V	
Speed disk recount number	N			992			
Disk recount out "L" level voltage	V _{DL}	I _D = -0.5mA			0.3	V	
Disk recount out "H" level voltage	V _{DH}	I _D = 0.5mA	V _{CC} -0.4			V	
Disk recount out leak current	I _{DI}				±1.0	μA	
Disk recount operation frequency	FD				1.0	MHz	*1
Oscillation range	Fosc				1.0	MHz	*1
Index bias current	I _{IDB}				±10	μA	
In-phase input voltage range	VID		1.5		V _{CC} -0.5	V	
Hysteresis setting current range			5	10	15	μA	
Index output "L" level voltage	VIDI	V _{ID} = 5V			0.4	V	
Index output "H" level voltage	VIDH	V _{ID} = 5V	4.5			V	
Break-down voltage		V _{ID} = 5V		2.50		V	
Delay output "L" level voltage	VDU	V _{ID} = 5V			0.4	V	
Delay output "H" level voltage	V _{DI H}	V _{ID} = 5V	4.5	<u> </u>		V	
Excessive heat protected operating temperature	TSD		150	180		°C	*1
Hysteresis width	∆TSD			40		°C	*1

Note: *1) Marked values (*1) are guaranteed by the design itself and therefore do not require measurement. *2) When hall-effect input becomes larger, kick-back occurs to the output waveform and for this reason, 200 m Vp-p or less is recommended.



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Pin Description

			Unit (resistance: Ω)					
Pin No.	Symbol	Pin voltage	Equivalent circuit	Pin description				
5 6 7 8 9 10	W- W+ V- V+ U- U*	2.2V min V _{CC} –0.7V max	6 200 10 77 9 10 77 9 10 77 9 10 77 77 9 10 77 77 9	 W-phase hall-effect input pin. W+ > W⁻ is established when logic is at an "H" level. V-phase hall-effect input pin. V+ > V⁻ is established when logic is at an "H" level. U-phase hall-effect input pin. U+ > U⁻ is established when logic is at an "H" level. 				
11	НВ	1.5V typ (I _H = 5mA)	O VCC	 Minus pin for hall-effect bias. When stopped, switches open and hall- effect bias severs. 				
12	FC			 Frequency characteristics revision pin By installing a capacitor between this pin and GND, close-loop oscillation for the current control system halts. 				
13 14	+ -	1.5V min V _{CC} –0.5V max	200 - Vcc 12 - 200 - 11 = 10,и А - 777 - 777 - 777 - 777	 Index input pin. When the I⁺ pin is at an "L" level, I1 operates with the fixed current of I1 = 10 μA and when at an "H" level, I1 does not flow. Hysteresis width is determined by the resistor attached externally to the I⁺ pin. 				
15	SL	"L": 0.8V max "H": 2.0V min	(15) 50 k 50 k 50 k 50 k 50 k 50 k 50 k 50 k	Time changeover pin. 1 : 1.2 "L" level : "H" level				
17	X1		€ 0 VCC 17 + 00	Reference clock generating pin.				
18	X2							
19	GND			Ground pin. Grounded as with pins 1 and 36.				

Continued on next page.

Continue	d from precedin	g page.	Unit (resistance: Ω)
Pin No.	Symbol	Pin voltage	Equivalent circuit	Pin description
20	ID	"L": 0.4V max "H": 4.5V min (When V _{ID} equals 5 V)	0 V _{ID} 10 k 20 → 10 k 20	Index pulse output pin.
21	DT1			Pin connecting the external CR for the delay time constant circuit.
22	DT2			Break-down current setting pin for the delay time constant circuit.
23	DTO	"L": 0.4V max "H": 4.5V min (When V _{ID} equals 5 V)	0 V I D 10 k 10 k 23 → 10 k 23 → 10 k 23	 Index delay pulse output pin.
24	FG0			• FG amplifier output pin.
25	FG-			FG amplifier negative input pin.
26	FG+	2.48V (When V _{ID} equals 5 V)		 FG amplifier positive input pin. Generates reference voltage within IC.
27	S/S1	"L": 0.8V max "H": 2.0V min	50k 50k 27) 50k 27) 50k 27)	• Start/stop changeover pin. "H" level active.
28	S/S2	"L": 0.8V max "H": 2.0V min	20 k 20 k 20 k 20 k 20 k 20 k 20 k 20 k	• Start/stop changeover pin. "L" level active.

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Continue	d from preceding	, page.	Unit (resistance: Ω)			
Pin No.	Symbol	Pin voltage	Equivalent circuit	Pin description		
29	DO			 Speed discriminator output pin. 		
30	IAI		30 → 30 → 31 → 3	Integrated amplifier input pin.		
31	IAO		³⁹ ≶ ^m → → → → → → → → → → → → → → → → → → →	Integrated amplifier output pin.		
32	VID		0 VCC	 Index pulse output and index delay pulse output power supply pin. For applications when V_{CC} equals 5 V, V_{CC} = V_{ID} = 5 V. 		
33	V _{CC}			 Total power supply voltage pin except for V_{ID}. Voltage must be stable and free of ripple and noise interference. 		
34	R _f			• Output current detection pin. By installing an R_f resistor between this pin and V_{CC} , output current is detected as voltage. Voltage detection at this pin activates the current limiter.		
35	U _{OUT}			U-phase output pin.		
36	Pow GND			Output transistor ground pin.		
1	Sub GND			Ground pin. Grounded as with pins 19 and 36.		
2 3	V _{OUT} W _{OUT}			V-phase output pin.W-phase output pin.		
4	AGC			AGC pin. Controls hall-effect amplifier gain in response to hall-effect input frequency.		

Truth Table

		Hall-Effect Input			
		U	V	W	
1	V-phase \rightarrow W-phase	н	н	L	
2	V-phase \rightarrow U-phase	L	Н	L	
3	W-phase \rightarrow U-phase	L	н	н	
4	W-phase \rightarrow V-phase	L	L	Н	
5	U-phase \rightarrow V-phase	Н	L	Н	
6	U-phase \rightarrow W-phase	н	L	L	

When an "H" level exists for hall-effect input,

 $U^{\scriptscriptstyle +} > U^{\scriptscriptstyle -}$

 $V^{\scriptscriptstyle +} > V^{\scriptscriptstyle -}$

 $W^{\scriptscriptstyle +} > W^{\scriptscriptstyle -}$

Index and Timing Chart



When SL equals an "H" level,

• T' ≈ 0.693CR6

$$\bullet t' \approx \frac{CR6R7}{R6+R7} \left\{ \ 0.405 + 1n \left(\frac{R6-R7}{R6-2R7} \right) \right\}$$

When SL equals an "L" level,

• T'
$$\approx 0.577 \text{CR6}$$

• t' $\approx \frac{\text{CR6R7}}{\text{R6} + \text{R7}} \left\{ 0.522 + \ln \left(\frac{0.781 \text{R6} - \text{R7}}{\text{R6} - 2 \text{R7}} \right) \right\}$

Using only the ID pulse involves shorting DT1 and DT2.



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